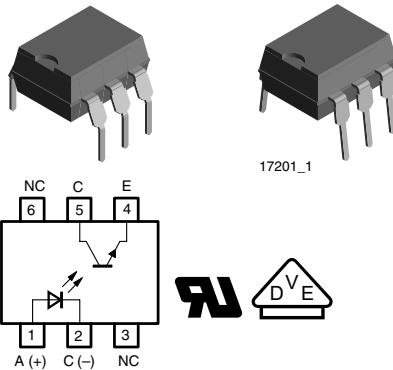


Optocoupler, Phototransistor Output



DESCRIPTION

The TCDT1100/TCDT1100G series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-pin plastic dual inline package. The base of the phototransistor is not connected providing noise immunity.

The elements are mounted on one leadframe which providing a fixed distance between input and output for highest safety requirements.

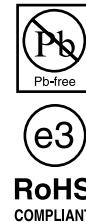
VDE STANDARDS

These couplers perform safety functions according to the following equipment standards:

- **DIN EN 60747-5-5 pending**
Optocoupler for electrical safety requirements
- **IEC 60950/EN 60950**
Office machines (applied for reinforced isolation for mains voltage $\leq 400 \text{ V}_{\text{RMS}}$)
- **VDE 0804**
Telecommunication apparatus and data processing
- **IEC 60065**
Safety for mains-operated electronic and related household apparatus

FEATURES

- Isolation test voltage $5300 \text{ V}_{\text{RMS}}$
- Extra low coupling capacity - typical 0.2 pF
- High common mode rejection
- No base terminal connection for improved noise immunity
- CTR offered in 4 groups
- Thickness though insulation $\geq 0.75 \text{ mm}$
- Creepage current resistance according to VDE 0303/ IEC 60112 comparative tracking index: CTI ≥ 275
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



APPLICATIONS

- Switch-mode power supplies
- Line receiver
- Computer peripheral interface
- Microprocessor system interface
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
 - for appl. class I - IV at mains voltage $\leq 300 \text{ V}$
 - for appl. class I - III at mains voltage $\leq 600 \text{ V}$
 according to DIN EN 60747-5-5.

AGENCY APPROVALS

- UL1577, file no. E76222 system code A, double protection
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-5
- FIMKO

ORDER INFORMATION

PART	REMARKS
TCDT1100	CTR > 40 %, DIP-6
TCDT1101	CTR 40 to 80 %, DIP-6
TCDT1102	CTR 63 to 125 %, DIP-6
TCDT1103	CTR 100 to 200 %, DIP-6
TCDT1100G	CTR > 40 %, DIP-6
TCDT1101G	CTR 40 to 80 %, DIP-6
TCDT1102G	CTR 63 to 125 %, DIP-6
TCDT1103G	CTR 100 to 200 %, DIP-6

Note

G = leadform 10.16 mm; G is not marked on the body.



ABSOLUTE MAXIMUM RATINGS ⁽¹⁾				
INPUT				
Reverse voltage		V _R	5	V
Forward current		I _F	60	mA
Forward surge current	t _p ≤ 10 µs	I _{FSM}	3	A
Power dissipation		P _{diss}	100	mW
Junction temperature		T _j	125	°C
OUTPUT				
Collector emitter voltage		V _{CEO}	32	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		I _C	50	mA
Collector peak current	t _p /T = 0.5, t _p ≤ 10 ms	I _{CM}	100	mA
Power dissipation		P _{diss}	150	mW
Junction temperature		T _j	125	°C
COUPLER				
Isolation test voltage (RMS)		V _{ISO}	5300	V _{RMS}
Total power dissipation		P _{tot}	250	mW
Ambient temperature range		T _{amb}	- 55 to + 100	°C
Storage temperature range		T _{stg}	- 55 to + 125	°C
Soldering temperature ⁽²⁾	2 mm from case, t ≤ 10 s	T _{sld}	260	°C

Notes

(1) T_{amb} = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	I _F = 50 mA	V _F		1.25	1.6	V
Junction capacitance	V _R = 0, f = 1 MHz	C _j		50		pF
OUTPUT						
Collector emitter voltage	I _C = 1 mA	V _{CEO}	32			V
Emitter collector voltage	I _E = 100 µA	V _{ECO}	7			V
Collector ermitter cut-off current	V _{CE} = 20 V, I _F = 0, E = 0	I _{CEO}		200		nA
COUPLER						
Collector emitter saturation voltage	I _F = 10 mA, I _C = 1 mA	V _{CEsat}			0.3	V
Cut-off frequency	V _{CE} = 5 V, I _F = 10 mA, R _L = 100 Ω	f _c		110		kHz
Coupling capacitance	f = 1 MHz	C _k		0.3		pF

Note

T_{amb} = 25 °C, unless otherwise specified.

Minimum and maximum values are testing requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I _O /I _F	V _{CE} = 5 V, I _F = 10 mA	TCDT1100	CTR	40			%
		TCDT1100G	CTR				%
		TCDT1101	CTR	40		80	%
		TCDT1101G	CTR				%
		TCDT1102	CTR	63		125	%
		TCDT1102G	CTR				%
		TCDT1103	CTR	100		200	%
		TCDT1103G	CTR				%

MAXIMUM SAFETY RATINGS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward current		I _F			130	mA
OUTPUT						
Power dissipation		P _{diss}			265	mW
COUPLER						
Rated impulse voltage		V _{IOTM}			6	kV
Safety temperature		T _{si}			150	°C

Note

According to DIN EN 60747-5-5 (see figure 1). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, t _{test} = 1 s	V _{pd}	1.6			kV
Partial discharge test voltage - lot test (sample test)	t _{Tr} = 60 s, t _{test} = 10 s, (see figure 2)	V _{IOTM}	6			kV
		V _{pd}	1.3			kV
Insulation resistance	V _{IO} = 500 V	R _{IO}	10 ¹²			Ω
	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹			Ω
	V _{IO} = 500 V, T _{amb} = 150 °C (construction test only)	R _{IO}	10 ⁹			Ω

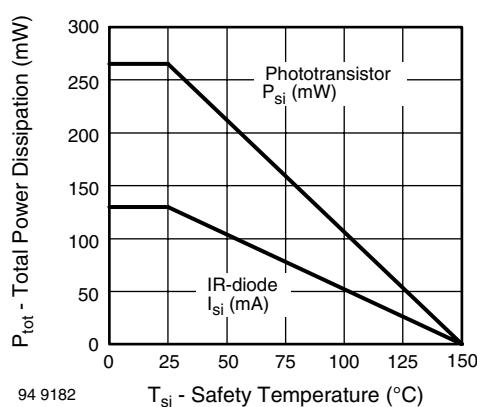


Fig. 1 - Derating Diagram

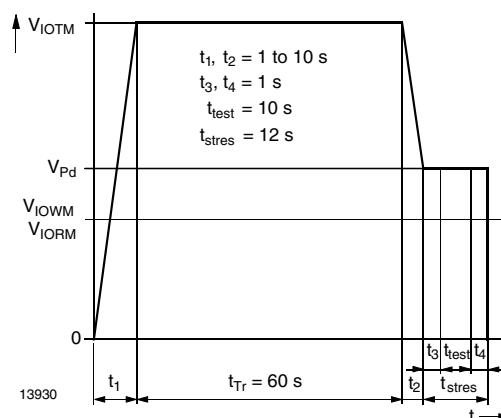


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5/DIN EN 60747-; IEC60747

SWITCHING CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5 \text{ V}$, $I_C = 5 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_d		4.0		μs
Rise time	$V_S = 5 \text{ V}$, $I_C = 5 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_r		7.0		μs
Fall time	$V_S = 5 \text{ V}$, $I_C = 5 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_f		6.7		μs
Storage time	$V_S = 5 \text{ V}$, $I_C = 5 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_s		0.3		μs
Turn-on time	$V_S = 5 \text{ V}$, $I_C = 5 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_{on}		11.0		μs
Turn-off time	$V_S = 5 \text{ V}$, $I_C = 5 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_{off}		7.0		μs
Turn-on time	$V_S = 5 \text{ V}$, $I_C = 10 \text{ mA}$, $R_L = 1 \text{k}\Omega$, (see figure 4)	t_{on}		25.0		μs
Turn-off time	$V_S = 5 \text{ V}$, $I_C = 10 \text{ mA}$, $R_L = 1 \text{k}\Omega$, (see figure 4)	t_{off}		42.5		μs

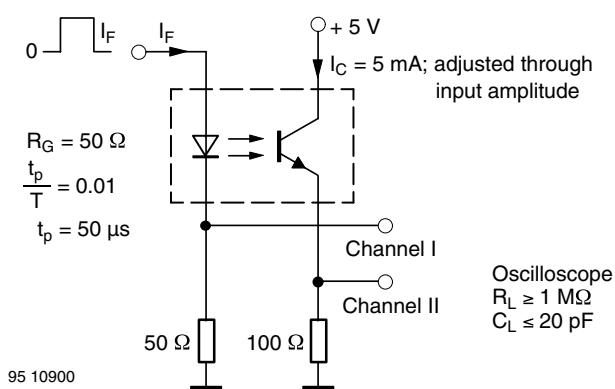


Fig. 3 - Test Circuit, Non-Saturated Operation

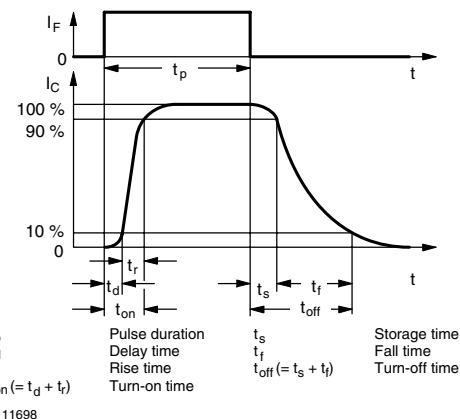


Fig. 5 - Switching Times

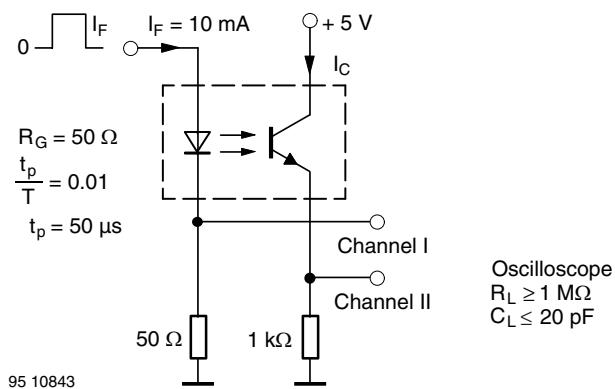


Fig. 4 - Test Circuit, Saturated Operation

TYPICAL CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

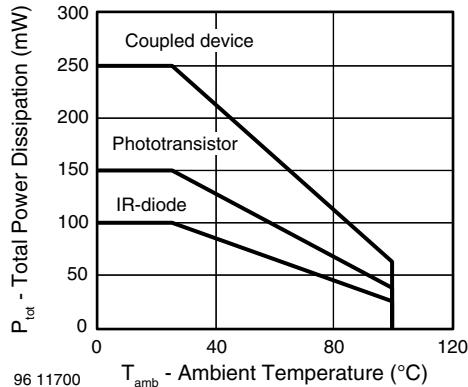


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

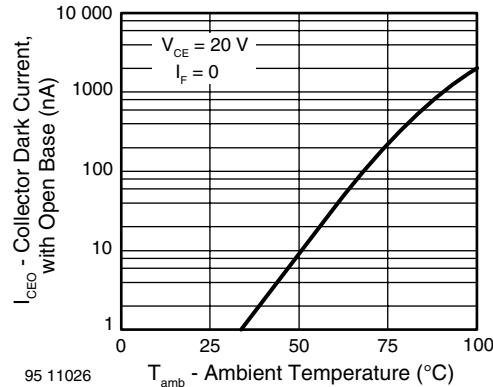


Fig. 9 - Collector Dark Current vs. Ambient Temperature

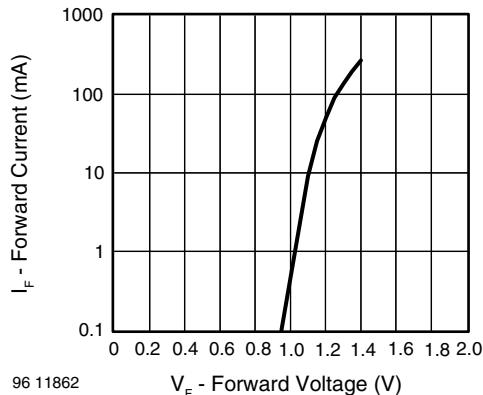


Fig. 7 - Forward Current vs. Forward Voltage

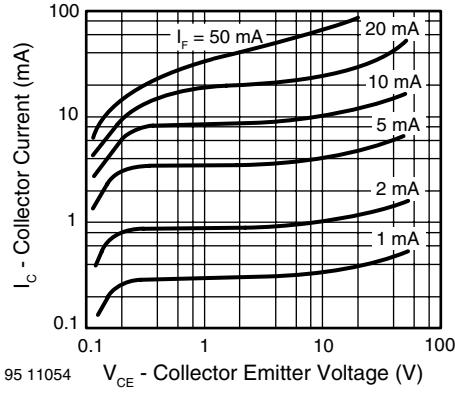


Fig. 10 - Collector Current vs. Collector Emitter Voltage

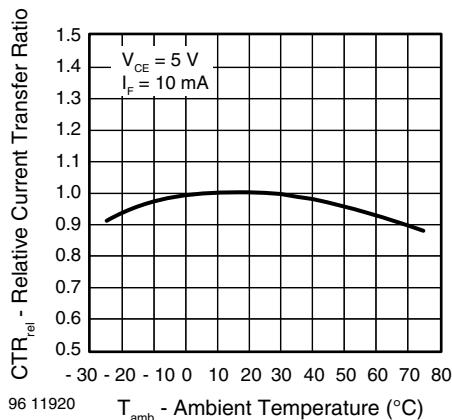


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

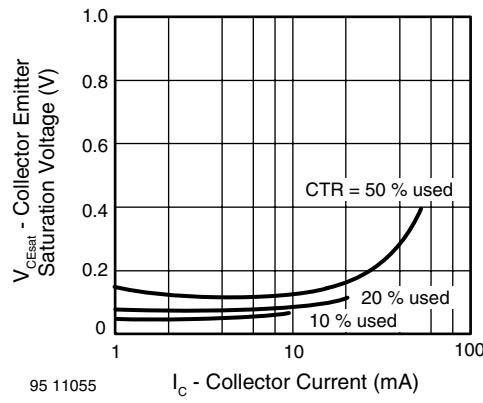


Fig. 11 - Collector Emitter Saturation Voltage vs. Collector Current

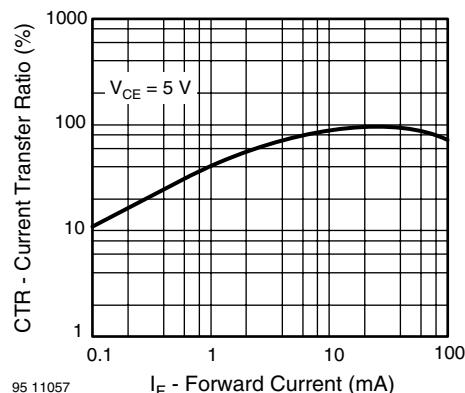


Fig. 12 - Current Transfer Ratio vs. Forward Current

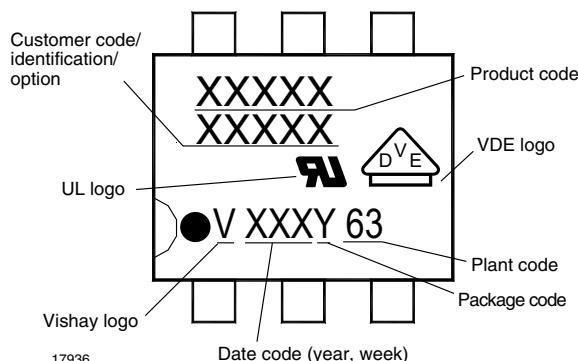


Fig. 15 - Marking Example

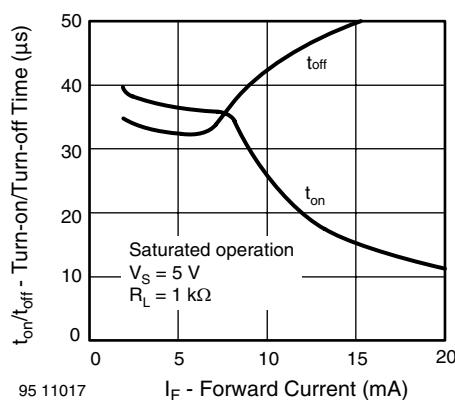


Fig. 13 - Turn-on/off Time vs. Forward Current

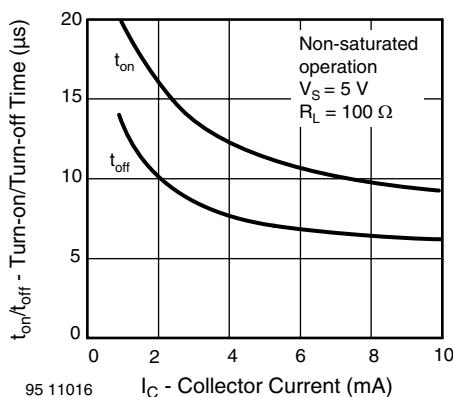


Fig. 14 - Turn-on/off Time vs. Collector Current

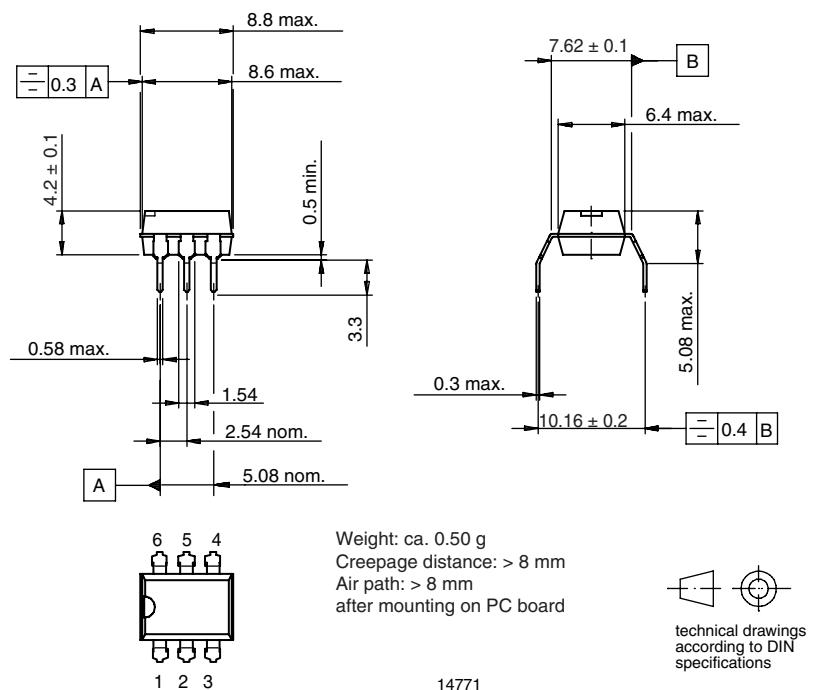
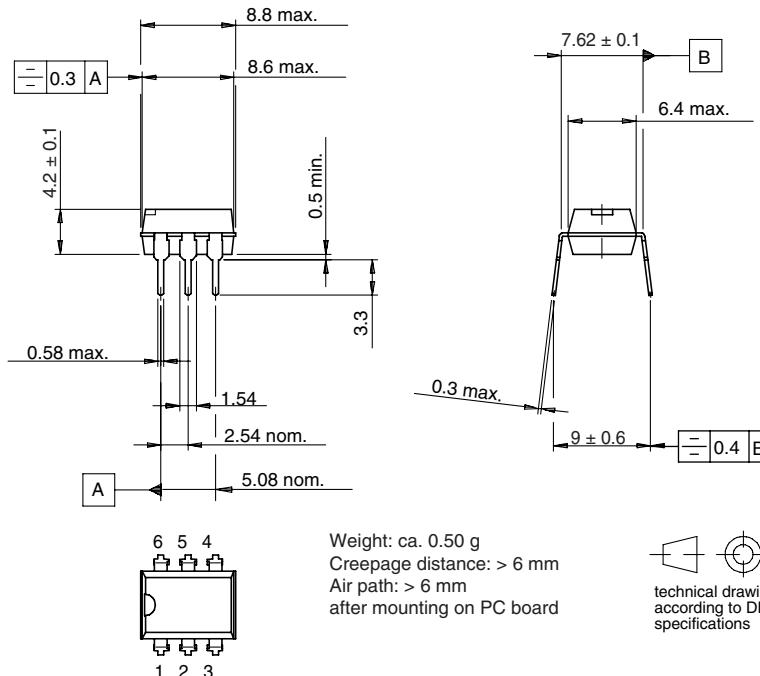
TCDT1100/TCDT1100G

Vishay Semiconductors

Optocoupler, Phototransistor Output



PACKAGE DIMENSIONS in millimeters



**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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ООО "ЛайфЭлектроникс"

"LifeElectronics" LLC

ИНН 7805602321 КПП 780501001 Р/С 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 30101810900000000703 БИК 044030703

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С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибуторских договоров

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- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
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Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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